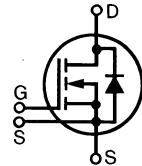


# CoolMOS Power MOSFET

**IXKN 40N60C**

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
<b>600 V</b>	<b>40 A</b>	<b>70 mΩ</b>

N-Channel Enhancement Mode  
Low  $R_{DS(on)}$ , High  $V_{DSS}$  MOSFET



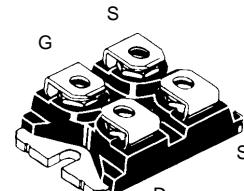
**COOLMOS**  
Power Semiconductors

Symbol	Conditions	Maximum Ratings		
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V	
$V_{GS}$		$\pm 20$	V	
$I_{D25}$	$T_C = 25^\circ\text{C}$	40	A	
$I_{D90}$	$T_C = 90^\circ\text{C}$	27	A	
$E_{AR}$	$I_D = 20 \text{ A}, L = 5 \mu\text{H}, T_{VJ} = 25^\circ\text{C}$ , repetitive	1	mJ	
$E_{AS}$	$I_D = 10 \text{ A}, L = 36 \text{ mH}, T_{VJ} = 25^\circ\text{C}$ , non repetitive	1.8	J	
$dv/dt$	$V_{DS} \leq V_{DSS}, I_S = 47 \text{ A}, di_S/dt = 100 \text{ A}/\mu\text{s}, T_J = T_{JM}$	6	V/ns	
$P_D$	$T_C = 25^\circ\text{C}$	290	W	
$T_J$		-40 ... +150	$^\circ\text{C}$	
$T_{JM}$		150	$^\circ\text{C}$	
$T_{stg}$		-40 ... +150	$^\circ\text{C}$	
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500	V~	
$M_d$	Mounting torque Terminal connection torque (M4)	1.5/13	Nm/lb.in.	
		1.5/13	Nm/lb.in.	

MOSFET Symbol	Conditions	Characteristic Values			
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$	600			V
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	0.5 50	25 $\mu\text{A}$	$\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 0.5 \cdot I_{D25}$			70	mΩ
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 2.5 \text{ mA}$	3.5		5.5	V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}, V_{DS} = 0$			$\pm 100$	nA

**miniBLOC, SOT-227 B**

 **E72873**



G = Gate  
S = Source  
D = Drain

Either source terminal at miniBLOC can be used as main or kelvin source

## Features

- miniBLOC package
  - Electrically isolated copper base
  - Low coupling capacitance to the heatsink for reduced EMI
  - High power dissipation due to AlN ceramic substrate
  - International standard package SOT-227
  - Easy screw assembly
- Fast CoolMOS power MOSFET
  - High blocking capability
  - Low on resistance
  - Avalanche rated for unclamped inductive switching (UIS)
  - Low thermal resistance due to reduced chip thickness
- Enhanced total power density

## Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating

CoolMOS is a trademark of  
Infineon Technologies AG.

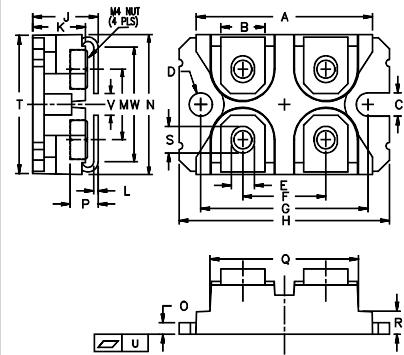
Symbol	Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10 \text{ V}; I_D = 0.5 \cdot I_{D25}$	30	S	
$C_{iss}$ $C_{oss}$ $C_{rss}$	$\left. \begin{array}{l} V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz} \\ \end{array} \right\}$	8.8 3.15 36	nF nF pF	
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$\left. \begin{array}{l} V_{GS} = 10 \text{ V}, V_{DS} = 350 \text{ V}, I_D = I_{D25} \\ \end{array} \right\}$	220 56 123	nC nC nC	
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	$\left. \begin{array}{l} V_{GS} = 10 \text{ V}, V_{DS} = 350 \text{ V}, I_D = 0.5 \cdot I_{D25} \\ R_G = 1.8 \Omega \text{ (External)} \end{array} \right\}$	28 95 100 10	ns ns ns ns	
$R_{thJC}$ $R_{thCK}$		0.05	0.43 K/W K/W	

**Source-Drain Diode****Characteristic Values**

Symbol	Conditions	min.	typ.	max.	
$V_{SD}$	$I_F = 0.5 \cdot I_{D25}, V_{GS} = 0 \text{ V}$	0.9	1.1	V	
$t_{rr}$ $I_{RM}$	$\left. \begin{array}{l} I_F = 47 \text{ A}, -di/dt = 100 \text{ A}/\mu\text{s}, \\ V_R = 350 \text{ V}, T_J = 25^\circ\text{C} \end{array} \right\}$	650 110		ns A	

**Package****Characteristic Values**

Symbol	Conditions	min.	typ.	max.	
Weight		30		g	

**miniBLOC, SOT-227 B**

M4 screws (4x) supplied

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	19.81	21.08